

SANYO SEMICONDUCTOR 2SD993

2SD993 NPN Triple Diffused Mesa Type Silicon Transistor
For H-Deflection Output (With Damper Diode)

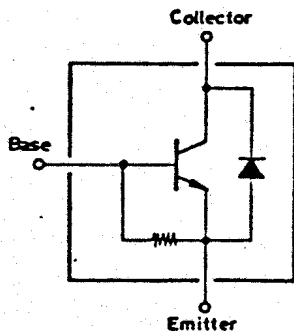
Absolute Maximum Ratings at Ta=25°C

Collector to Base Voltage	V _{CB0}	1500	V	
Collector to Emitter Voltage	V _{CEO}	600	V	
Emitter to Base Voltage	V _{EBO}	6	V	
Collector Current	I _C	3	A	
Collector Current (peak)	i _{cp}	6	A	
Collector Dissipation	P _C	3	W	
	P _C	T _c =25°C	50	W
Junction Temperature	T _j	150	°C	
Storage Temperature	T _{stg}	-40~+150	°C	

Electrical Characteristics at Ta=25°C

			min	typ	max	unit
Collector Cut off Current	I _{CES}	V _{CB} =1500V, V _{EB} =0			1.0	mA
Emitter Cut off Current	I _{EBO}	V _{BE} =4V, I _C =0	44		133	mA
Emitter to Base Voltage	V _{EBO}	I _E =200mA, I _C =0	6.0			V
Emitter to Collector Voltage	V _{ECO}	I _E =2A, I _B =0			2.0	V
DC Current Gain	h _{FE}	V _{CE} =5V, I _C =2A	3		15	
C-E Saturation Voltage	V _{CE(sat)}	I _C =2.5, I _B =0.6A			10	V
B-E Saturation Voltage	V _{BE(sat)}	I _C =2.5, I _B =0.6A			1.3	V
C-E sustain Voltage	V _{CE(sus)}	I _C =100mA, I _B =0, L=35mH	600			V
Fall Time	t _f	I _C =2.5A, I _B =0.5A, t=10 90%			1.0	µs
		T _c =80°C				

Equivalent Circuit



Case Outline (unit:mm)

